



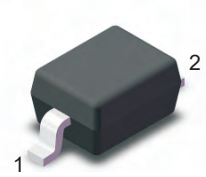
SD103AWB~SD103CWB

Schottky Barrier Diodes

Features

- Low Capacitance
- Low Forward Voltage Drop

SOD-323W



1.Cathode  2.Anode

Marking Code :
SD103AWB: S4
SD103BWB: S5
SD103CWB: S6

Absolute Maximum Ratings at $T_A = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Value	Unit
Maximum Repetitive Peak Reverse Voltage	SD103AWB SD103BWB SD103CWB	V_{RRM} 40 30 20	V
Reverse Voltage	SD103AWB SD103BWB SD103CWB	V_R 40 30 20	V
Average Forward Rectified Current	$I_{F(AV)}$	350	mA
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load (JEDEC method)	I_{FSM}	2	A
Power Dissipation	P_D	200	mW
Junction Temperature	T_J	125	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-55 to +150	$^\circ\text{C}$



SD103AWB~SD103CWB

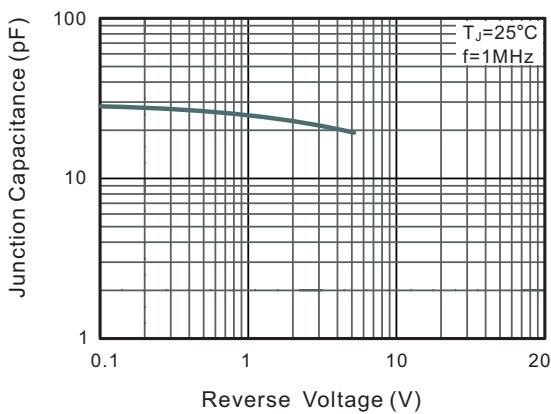
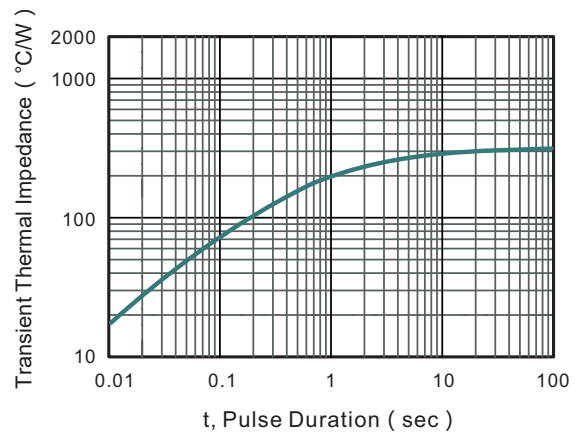
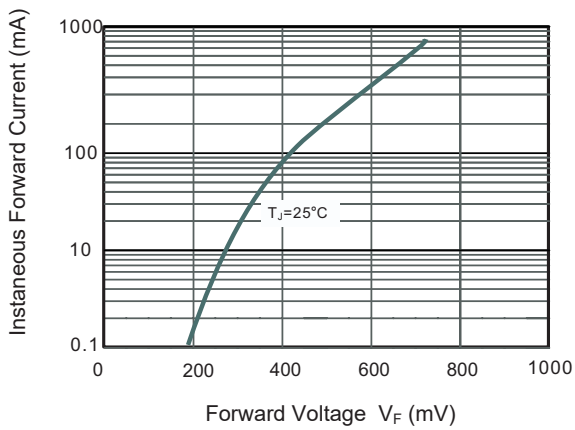
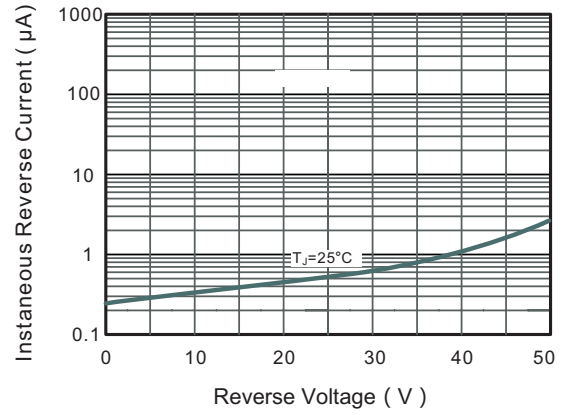
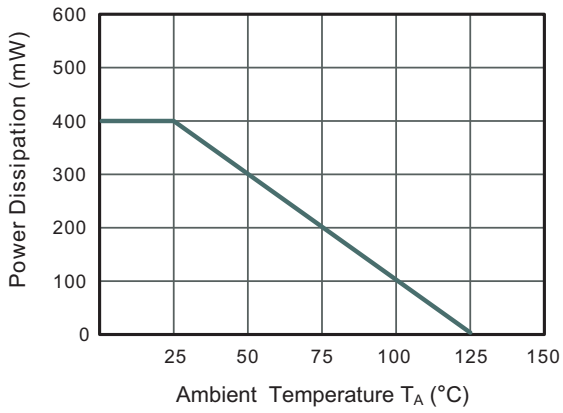
Schottky Barrier Diodes

Characteristics at $T_A = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 100\text{ }\mu\text{A}$	$V_{(BR)R}$	40	--	--	V
SD103AWB					
SD103BWB		30	--	--	
SD103CWB		20	--	--	
Forward Voltage at $I_F = 20\text{ mA}$	V_F	--	--	0.37	V
at $I_F = 200\text{ mA}$		--	--	0.6	
Reverse Leakage Current at $V_R = 30\text{ V}$	I_R	--	--	5	μA
SD103AWB					
at $V_R = 20\text{ V}$		--	--	5	
SD103BWB					
at $V_R = 10\text{ V}$		--	--	5	
SD103CWB					
Total Capacitance at $V_R = 0\text{ V}$, $f = 1\text{ MHz}$	C_T	--	50	--	pF
Reverse Recovery Time at $I_F = I_R = 200\text{ mA}$, $I_{rr} = 0.1 I_R$, $R_L = 100\text{ }\Omega$	T_{rr}	--	10	--	nS



Typical Characteristic Curves





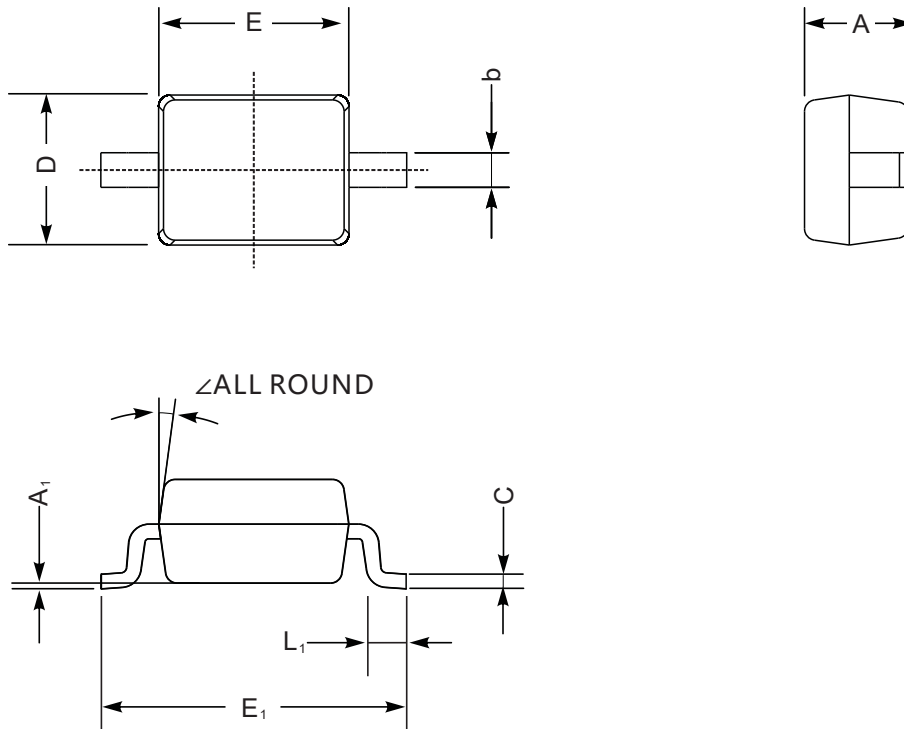
SD103AWB~SD103CWB

Schottky Barrier Diodes

Package Outline

SOD-323W

Dimensions in mm



UNIT		A	C	D	E	E ₁	b	L ₁	A ₁	∠
mm	max	1.1	0.15	1.4	1.8	2.75	0.4	0.45	0.2	9°
	min	0.8	0.08	1.2	1.4	2.55	0.25	0.2	—	
mil	max	43	5.9	55	70	108	16	16	8	
	min	32	3.1	47	63	100	9.8	7.9	—	